

GL882

NPN EPITAXIAL PLANAR TRANSISTOR

Description

The GL882 is suited for the output stage of 2W audio, voltage regulator ,and relay driver.

Package Dimension

SOT - 223

Marking :

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.70	7.30	B	13° TYP.	
C	2.90	3.10	J	2.30 REF.	
D	0.02	0.10	1	6.30	6.70
E	0°	10°	2	6.30	6.70
I	0.60	0.80	3	3.30	3.70
H	0.25	0.35	4	3.30	3.70
			5	1.40	1.80

Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C
Collector to Base Voltage at Ta=25	VCBO	40	V
Collector to Emitter Voltage at Ta=25	VCEO	30	V
Emitter to Base Voltage at Ta=25°C	VEBO	5.0	V
Collector Current at Ta=25°C	IC	3.0	A
Total Power Dissipation at Ta=25°C	PD	2	W

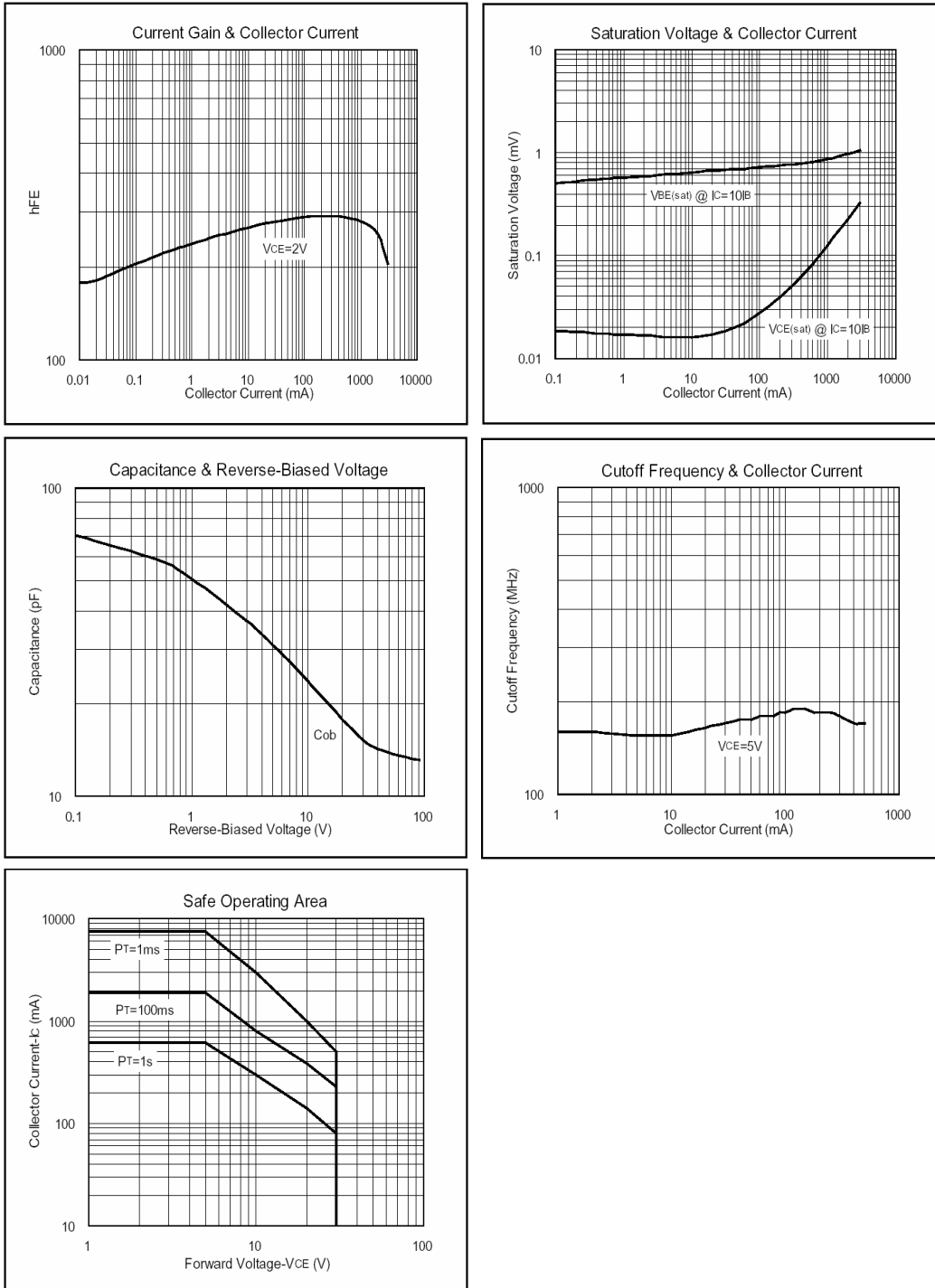
Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	40	-	-	V	IC=100uA, IE=0
BVCEO	30	-	-	V	IC=1mA, IB=0
BVEBO	5	-	-	V	IE=10uA
ICBO	-	-	1	uA	VCB=30V
IEBO	-	-	1	uA	VEB=3V
VCE(sat)	-	-	0.5	V	IC=2A, IB=0.2A
VBE(sat)	-	-	2	V	IC=2A, IB=0.2A
hFE1	30	-	-	-	VCE=2V, IC=20mA
hFE2	100	-	500	-	VCE=2V, IC=1A
FT	-	90	-	MHz	VCE=5V, IC=0.1A, f=100MHz
Cob	-	45	-	Pf	VCB=10V, IE=0, f=1MHz

Classification Of hFE

Rank	Q	P	E
Range	100-200	160-320	250-500

Characteristics Curve



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